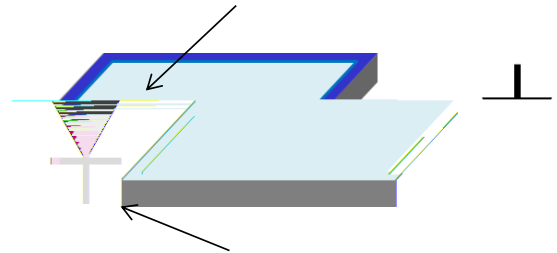


YJ Planar Schottky Barrier Diode Die Specification

200V 3A, 60mil, Schottky barrier diode die based on silicon planar process
 Part No.: PSB060H200SS-280A



Main Products Characteristics

Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	V_{RRM}	200 V
Average forward current	$I_{F(AV)}$	3A
($t_p = 8.3$ ms, halfwave, 1 cycle)	I_{FSM}	80 A
Storage temperature range	T_{stg}	-50 to +175 °C
Maximum operating junction temperature	T_j	175 °C

Static Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	
		Spec	Typical
Reverse breakdown voltage $I_R = 1\text{mA}$	V_{BR}	210 V	230V
Maximum forward voltage drop $I_F = 3\text{A}$	V_F	0.85V	0.80V
		2%	
Maximum reverse current $V_R = V_{RRM}$	I_R	5uA	0.2uA
		2%	

Device Schematics and Outline Drawing

Die Thickness *	11 Mils
Die Size **	60 Mils
Top Metal Pad	56 Mils
Active Area	52 Mils
Top Metal	Ag
Back Metal	Ag

Note: 1 * : Also can offer device with 8 mils thickness
 2 **: Cutting street width is around 1.5 mils

Important Notice

<p>Specification apply to die only. Actual performance may degrade when assembled.</p> <p>does not guarantee device performance after assembly.</p> <p>All operating parameters must be validated for each customer application by customer's technical experts.</p> <p>Data sheet information is subjected to change without notice.</p>	<p>Recommended Storage Environment:</p> <p>Store in original container, in dessicated nitrogen, with no contamination.</p> <p>Shelf life for parts stored in above condition is 2 years.</p> <p>If the storage is done in normal atmosphere shelf life is reduced to 6 months.</p>
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